

WHAT IS CLAIMED IS:

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1. A semiconductor light-emitting device having a DBR (Distributed Bragg Reflector) and a light-emitting layer formed on a GaAs substrate, the DBR being located between the GaAs substrate and the light-emitting layer, in which light directed from the light-emitting layer toward a top surface has a radiation angle dependence, the semiconductor light-emitting device further comprising:

10 a semiconductor layer having a number of layers of 1 or more is formed on the light-emitting layer, a top surface of the semiconductor layer being a roughened surface.

2. The semiconductor light-emitting device according to Claim 1, wherein the light-emitting layer to be formed on the GaAs substrate is a single layer or a plurality of layers made of  $Al_yGa_zIn_{1-y-z}P$  ( $0 \leq y \leq 1$ ,  $0 \leq z \leq 1$ ).

15 3. The semiconductor light-emitting device according to Claim 1, wherein the semiconductor layer whose top surface is a roughened surface is made of  $Al_xGa_{1-x}As$  ( $0 \leq x \leq 1$ ).

20 4. The semiconductor light-emitting device according to Claim 3, wherein the semiconductor layer made of  $Al_xGa_{1-x}As$  ( $0 \leq x \leq 1$ ) is transparent to an emission wavelength.

5. The semiconductor light-emitting device according to Claim 3, wherein the semiconductor layer made of  $Al_xGa_{1-x}As$  ( $0 \leq x \leq 1$ ) has an Al mixed crystal ratio x of 0.5 - 0.8.

6. The semiconductor light-emitting device according to Claim 3, further comprising an  $Al_yGa_zIn_{1-y-z}P$  ( $0 \leq y \leq 1$ ,  $0 \leq z \leq 1$ ) layer for diffusing a current injected from an electrode provided on a light takeout side, the  $Al_yGa_zIn_{1-y-z}P$  layer being provided between the semiconductor layer made of  $Al_xGa_{1-x}As$  ( $0 \leq x \leq 1$ ) and the light-emitting layer.

5 7. The semiconductor light-emitting device according to Claim 1, wherein the layer whose top surface is a roughened surface is made of  $Al_yGa_zIn_{1-y-z}P$  ( $0 \leq y \leq 1$ ,  $0 \leq z \leq 1$ ).

10 8. The semiconductor light-emitting device according to Claim 7, wherein the layer whose top surface is a roughened surface has a lattice constant different by 0.5% or more from that of the GaAs substrate.

15 9. A method for manufacturing a semiconductor light-emitting device having a DBR (Distributed Bragg Reflector) and a light-emitting layer formed on a GaAs substrate, the DBR being located between the GaAs substrate and the light-emitting layer, in which light directed from the light-emitting layer toward a top surface has a radiation angle dependence, the semiconductor light-emitting device manufacturing method comprising the steps of:

20 forming a semiconductor layer having a number of layers of 1 or more on the light-emitting layer; and thereafter roughing a wafer surface.

10. The method for manufacturing a semiconductor light-emitting device according to Claim 9, wherein the step of roughing the wafer surface includes a step of forming a pattern for scattering light onto the wafer 5 surface by photolithography and etching.

11. The method for manufacturing a semiconductor light-emitting device according to Claim 9, wherein the step of roughing the wafer surface includes a step of abrasion the wafer surface.

10 12. The method for manufacturing a semiconductor light-emitting device according to Claim 9, wherein the step of forming the semiconductor layer having a number of layers of 1 or more on the light-emitting layer includes a step of forming a semiconductor layer including an  $\text{Al}_y\text{Ga}_z\text{In}_{1-y-z}\text{P}$  ( $0 \leq y \leq 1$ ,  $0 \leq z \leq 1$ ) layer, and the step of roughing the wafer 15 surface includes a step of boiling the wafer in hydrochloric acid.

13. A method for manufacturing a semiconductor light-emitting device having a DBR (Distributed Bragg Reflector) and a light-emitting layer formed on a GaAs substrate, the DBR being located between the GaAs substrate and the light-emitting layer, in which light directed from the light-emitting layer toward a top surface has a radiation angle dependence, the semiconductor light-emitting device 20 25 manufacturing method comprising the steps of:

forming on the light-emitting layer a semiconductor layer having a number of layers of 1 or more including an  $Al_yGa_zIn_{1-y-z}P$  ( $0 \leq y \leq 1$ ,  $0 \leq z \leq 1$ ) layer having a lattice constant different by 0.5% or more from the GaAs substrate, thereby roughing a wafer surface.

14. The method for manufacturing a semiconductor light-emitting device according to Claim 9, wherein the step of forming on the light-emitting layer a semiconductor layer having a number of layers of 1 or more includes a step of forming on the light-emitting layer a semiconductor layer including an  $Al_yGa_zIn_{1-y-z}P$  ( $0 \leq y \leq 1$ ,  $0 \leq z \leq 1$ ) layer and an  $Al_xGa_{1-x}As$  ( $0 \leq x \leq 1$ ) layer, and the step of roughing the wafer surface includes a step of treating with dilute hydrofluoric acid or dilute nitric acid.

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